

SUBSTRATE PROCESSING APPARATUS, METHOD OF MANUFACTURING SEMICONDUCTOR DEVICE, AND RECORDING MEDIUM

ABSTRACT

There is provided a technique that includes (a) a process chamber configured to accommodate a plurality of substrates arranged vertically, provided with a product region and a dummy region and including a main exhauster on a lateral side thereof, (b) a first injector extending vertically within the process chamber on an opposite side from the main exhauster, and configured to supply a first precursor toward the substrates accommodated in the product region and the dummy region, (c) at least one selected from the group of a second injector and a third injector, wherein the second injector supplies an assist gas for diluting the first precursor toward substrates and the third injector supplies an inert gas toward the substrates accommodated in the product region and the substrates accommodated in the dummy region; and (d) a fourth injector configured to supply an inert gas only to the dummy region.

Fig. 1